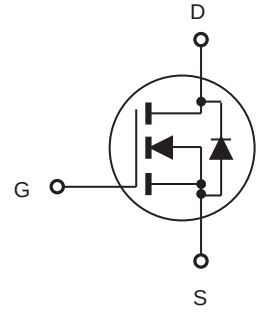
CEP740A/CEB740A
CEI740A/CEF740A

N-Channel Enhancement Mode Field Effect Transistor

FEATURES

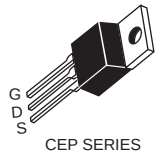
Type	V_{DSS}	$R_{DS(ON)}$	I_D	@V_{GS}
CEP740A	400V	650mΩ	10A	10V
CEB740A	400V	650mΩ	10A	10V
CEI740A	400V	650mΩ	10A	10V
CEF740A	400V	650mΩ	10A [e]	10V

- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handing capability.
- Lead free product is acquired.
- TO-220 & TO-263 & TO-262 package & TO-220F full-pak for through hole.

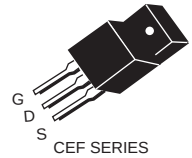


CEB SERIES
TO-263(DD-PAK)

CEI SERIES
TO-262(I2-PAK)



CEP SERIES
TO-220



CEF SERIES
TO-220F

ABSOLUTE MAXIMUM RATINGS T_C = 25°C unless otherwise noted

Parameter	Symbol	Limit		Units
		TO-220/263/262	TO-220F	
Drain-Source Voltage	V_{DS}	400		V
Gate-Source Voltage	V_{GS}	±30		V
Drain Current-Continuous	I_D	10	10 [e]	A
Drain Current-Pulsed [a]	I_{DM} [f]	40	40 [e]	A
Maximum Power Dissipation @ T_C = 25°C	P_D	125	43	W
- Derate above 25°C		1	0.34	W/°C
Single Pulsed Avalanche Energy [d]	E_{AS}	400	400	mJ
Single Pulsed Avalanche Current [d]	I_{AS}	10	10	A
Operating and Store Temperature Range	T_J,T_{stg}	-55 to 150		°C

Thermal Characteristics

Parameter	Symbol	Limit		Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.0	2.9	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	65	°C/W

查询"CEI740A"供应商

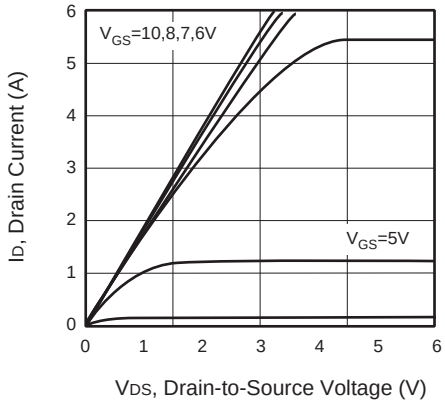


Figure 1. Output Characteristics

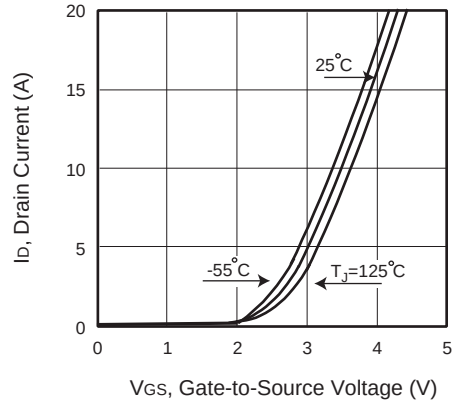


Figure 2. Transfer Characteristics

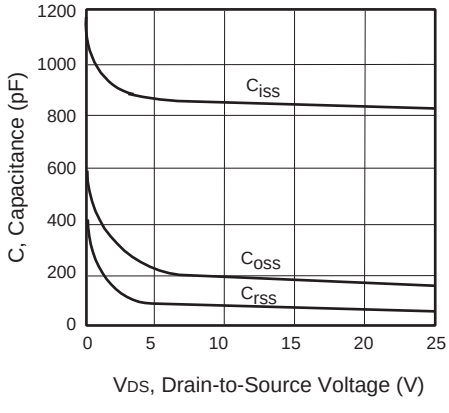


Figure 3. Capacitance

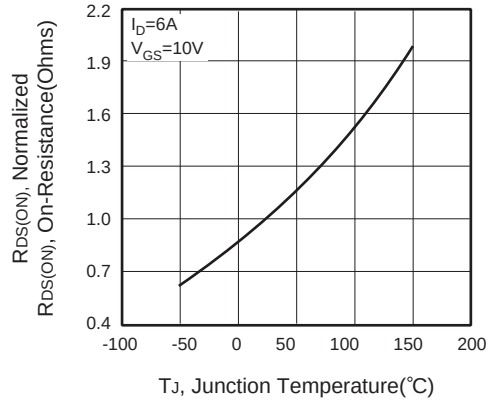


Figure 4. On-Resistance Variation with Temperature

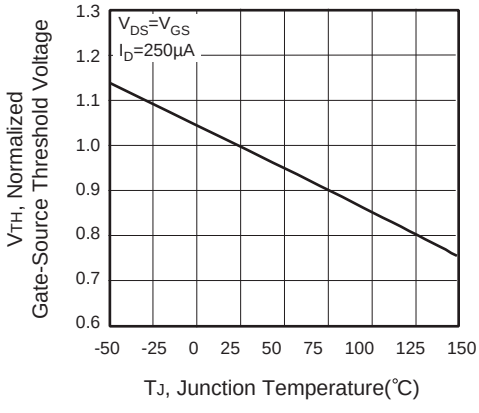


Figure 5. Gate Threshold Variation with Temperature

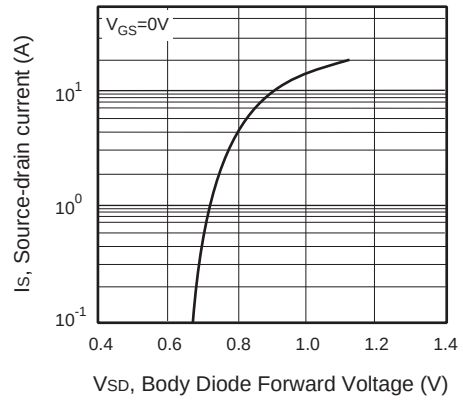


Figure 6. Body Diode Forward Voltage Variation with Source Current

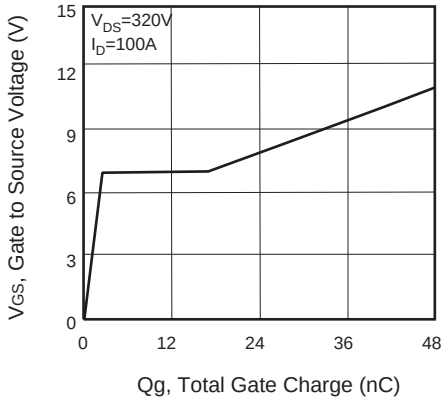


Figure 7. Gate Charge

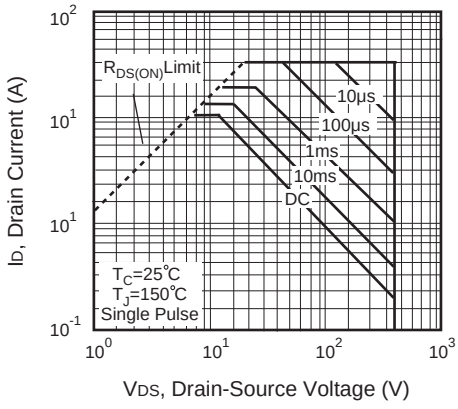


Figure 8. Maximum Safe Operating Area

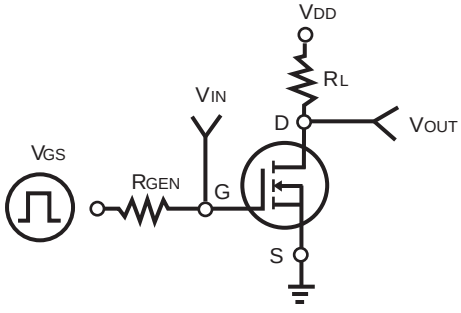


Figure 9. Switching Test Circuit

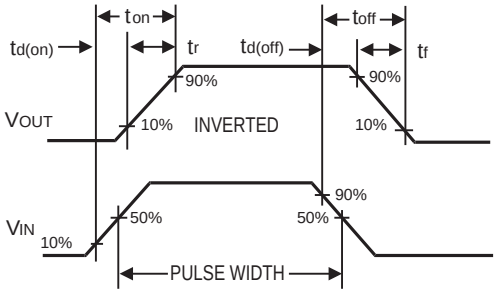


Figure 10. Switching Waveforms

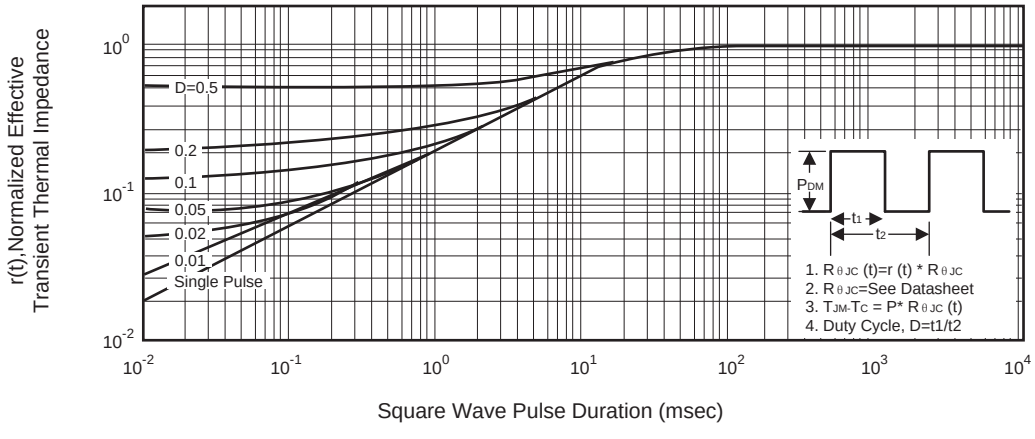


Figure 11. Normalized Thermal Transient Impedance Curve